The Optical, Structural and Electrical Properties of DC Magnetron Sputtered Al-1%-Si Alloy

Structural and Electrical Properties of Thin Palladium Layers on Epitaxial Si1-X-Gex/Si

Structural and Electrical Properties of In-implanted Ge

Structural and Electrical Properties of MnO Films Grown by Pulsed Laser Deposition

Structural and Electrical Properties of 0.65PMN-0.35PT Thick Films on Different Substrates

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Semiconductors

The Structural and Electrical Properties of Thin Films Sputtered from a Platinum Cathode in Argon-oxygen Mixtures

Thermal, Infrared, Structural and Electrical Properties of Copper (II) Benzoate Derivatives Here, we report on the effects of dopant concentration on the structural and electrical properties of In-implanted Ge. For In concentrations of \( \leq 0.2 \) at. \%, extended x-ray absorption fine structure and x-ray absorption near-edge structure measurements demonstrate that all In atoms occupy a substitutional lattice site while metallic In precipitates are apparent in transmission electron micrographs for In concentrations \( \geq 0.6 \) at. \%. Evidence of the formation of In-vacancy complexes deduced from extended x-ray absorption fine structure measurements is complimented by density functional theory simulations. Hall effect measurements of the conductivity, carrier density, and carrier mobility are then correlated with the substitutional In fraction.

Structural and Electrical Properties of Zirconia Doped with Some Oxides

The Structural and Electrical Properties of Manganese Telluride

Structural and Electrical Properties of \( \text{Y}_1 \text{Cr}_{x-y} \text{Mn}_x \text{Co}_y \text{O}_3 \)

The Structural and Electrical Properties of Some Liquid Transition Metal-chalcogenide Alloys

Structural and Electrical Properties of Li-doped TiO\(_2\) Rutile Ceramics

The Structural and Electrical Properties of Thin GaAs Films Deposits, by radio frequency magnetron sputtering disposition, thin films of fluorine doped zinc oxide onto polyethylene naphthalate and glass substrates at room temperature. Studies of the effects of post disposition annealing by argon and a gas mixture of argon and hydrogen on the structural and electrical properties of the films deposited on polyethylene naphthalate and glass.

Structural and Electrical Properties of Substituted Potassium Tantalate System

Epitaxially Stabilized Iron-silicides

Structural and Electrical Properties of Indium Phosphide Anodic Oxides

Structural and Electrical Properties of Radio Frequency Sputtered Fluorine Doped Zinc Oxide Films

Structural and Electrical Properties of Some Manganites Compounds Colossal magnetoresistive (CMR) compounds with the perovskite structure are mainly characterized by a competition between ferromagnetism and paramagnetism, and between a metallic and insulator behavior. Electrical and structure have been studied in \( \text{La}_1-x\text{Sr}_x\text{MnO}_y \) (\( x = 0.1, 0.15, 0.2, 0.25, 0.3, 0.35 \)). The magnetoresistance was determined by measuring the temperature dependence of resistivity under a magnetic field \( 0.5 \) T. It was negative for all compositions and significantly influenced by the Sr content and annealing time. The obtained magnetoresistance values may make the materials promising for different applications.
Structural and electrical properties of ZnTe-Ge heterojunctions

Structural and Electrical Properties of Thin Films and Superlattices Composed of II-VI Semiconductors

Structural and electrical properties of metallic epitaxial silicide films

Structural and Electrical Properties of Iron/magnesium-oxide/gallium-arsenide Heterostructures

Phase Diagram, and Structural and Electrical Properties of Pyrochlores in Bi2O3-ZnO-Nb2O5 Ternary System

Processing, Structural and Electrical Properties of SiC

Structural and Electrical Properties of Graphite Intercalation Compounds and Graphite Fiber Compounds

Structural and Electrical Properties of Some Organic Semiconductors

Structural and Electrical Properties of Thin Deposited Single Crystal Germanium Films

Structural and Electrical Properties of Epitaxial Cerium Oxide on Silicon Substrates

The Growth, Thermal Stability, and Structural and Electrical Properties of Doped and Undoped Si-based Epitaxial Structures

Structural and Electrical Properties of Nanocrystals Produced by Ion Implantation in Thin SiO2 Films

The Structural and Electrical Properties of Manganese Telluride

Understanding the Thermal, Structural, and Electrical Properties of the High Entropy Ceramics, High Entropy Oxides and Carbides, Using Computational Modeling

Structural and Electrical Properties of Diamond Thin Films

Studies on the Growth, Structural and Electrical Properties of Silicon-based Heterostructure Nanowires

Structural and Electrical Properties of Si-rich Silicon Nitride: Its Application in Current Enhancement Injection

Structural and Electrical Properties of Silicon/nickel Disilicide Interfaces

Structural and Electrical Properties of Ion Beam Synthesised Ternary Iron-cobalt Silicide

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